

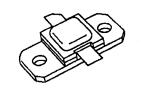
140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013 PHONE: (215) 631-9840 FAX: (215) 631-9855

MS2213

RF & MICROWAVE TRANSISTORS AVIONICS/JTIDS APPLICATIONS

Features

- 960-1215 MHz
- COMMON BASE
- GOLD METALLIZATION
- HERMETIC PACKAGE
- CLASS C OPERATION
- POUT = 30 W MIN. WITH 7.8 dB GAIN

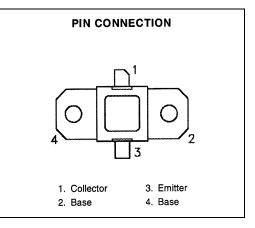


.400 x .400 2LFL M214 hermetically sealed

DESCRIPTION:

The MS2213 is a silicon NPN bipolar device specifically designed for JTIDS pulsed power applications from 960-1215 MHz.

Gold metallization and emitter ballasting assure high reliability under Class C amplifier operation. This device operates over a wide range of pulse widths, duty cycles and temperatures, and can withstand a 15:1 VSWR mismatch under load.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{cc}	Collector-Supply Voltage	40	V
Ι _c	Device Current	3.5	A
P _{DISS}	Power Dissipation	75	w
TJ	Junction Temperature (RF Pulsed Operation)	+250	°C
T _{STG}	Storage Temperature	-65 to +200	°C

Thermal Data

R _{TH(J-C)} Junction-case Thermal Resistance	2.2	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Тур.	Max.	Unit
BV _{CBO}	I _c = 10mA	55			v
BV _{EBO}	I _E = 1mA	3.5			v
BV _{CER}	$I_{C}= 20 \text{mA}$ $R_{BE}=10 \Omega$	55			v
I _{CES}	V _{CB} = 35 V			5.0	mA
h _{FE}	V _{CE} = 5 V I _C = 1A	15		150	

DYNAMIC

Symbol	Test Conditions			Value			
Symbol Test Conditions		3	Min.	Тур.	Max.	Unit	
Pout	f = 960-1215 MHz	$V_{CC} = 35V$	P _{IN} =5.0W	30			W
G _₽	f = 960-1215 MHz	$V_{CC} = 35V$	P _{IN} =5.0W	7.8			dB
ηc	f = 960-1215 MHz	V _{cc} =35V	P _{IN} =5.0W	40			%

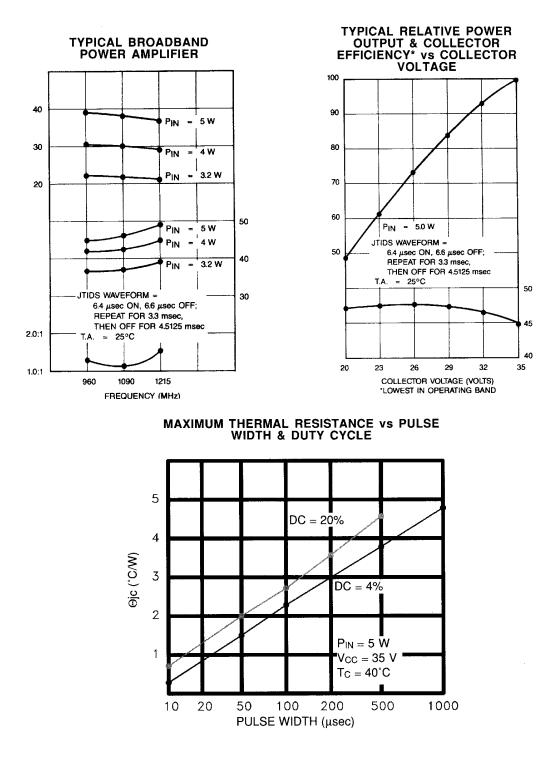
Pulse format: 6.4 us on 6.6 us off, repeat for 3.3ms, then off for 4.5125 ms. Duty Cycle: Burst 49.2%, overall 20.8%.

IMPEDANCE DATA

Freq. (MHz)	Ζ_{IN} (Ω)	Ζ _{ουτ} (Ω)		
960	4.5 + j 6.0	11.0 + j 0.5		
1090	5.5 + j 6.3	12.0 – j 2.0		
1215	5.0 + j 5.0	12.5 – j 5.0		

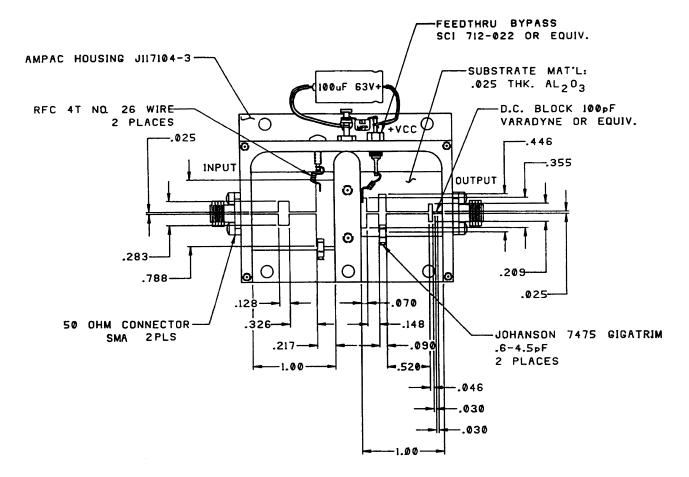


TYPICAL PERFORMANCE





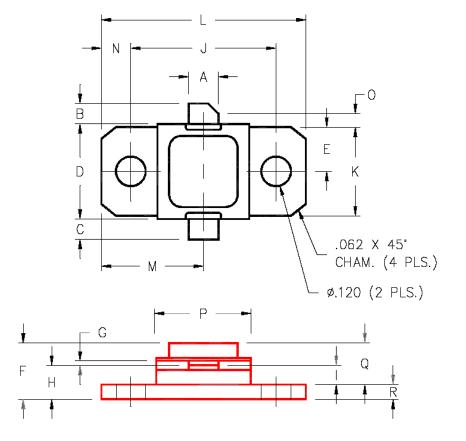
TEST CIRCUIT





PACKAGE MECHANICAL DATA

PACKAGE STYLE M214



	MINIMUM	MAXIMUM		MINIMUM	MAXIMUM		
	INCHES/MM	INCHES/MM		INCHES/MM	INCHES/MM		
А	.140/3,56		.140/3,56		J	.650/	′16,51
В	.110/2,80		K	.386/9,80			
С	.110/2,80		L	.900/22.86			
D	.395/10,03	.407/10,34	М	.450/11,43			
Ε	.193/4,90		Ν	.125/3,18			
F		.230/5,84	0	.050/1,27			
Ĝ	.003/0,08	.006/0,15	Ρ	.405/10,29			
Н	.118/3,00	.131/3,33	Q	.170/4,32			
]	.063/1,60		R	.062/1,58			

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